

# 2SD1994A

## Silicon NPN epitaxial planar type

For low-frequency power strengthening and drive

Complementary to 2SB1322A

### ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Allowing supply with the radial taping

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_C$	1	A
Peak collector current	$I_{CP}$	1.5	A
Collector power dissipation *	$P_C$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \*: Printed circuit board: Copper foil area of 1  $\text{cm}^2$  or more, and the board thickness of 1.7 mm for the collector portion

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	60			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$
Forward current transfer ratio * <sup>1</sup>	$h_{FE1}$ * <sup>2</sup>	$V_{CE} = 10 \text{ V}, I_C = 500 \text{ mA}$	85		340	—
	$h_{FE2}$	$V_{CE} = 5 \text{ V}, I_C = 1 \text{ A}$	50			—
Collector-emitter saturation voltage * <sup>1</sup>	$V_{CE(sat)}$	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.2	0.4	V
Base-emitter saturation voltage * <sup>1</sup>	$V_{BE(sat)}$	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.85	1.20	V
Transition frequency * <sup>1</sup>	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		11	20	pF

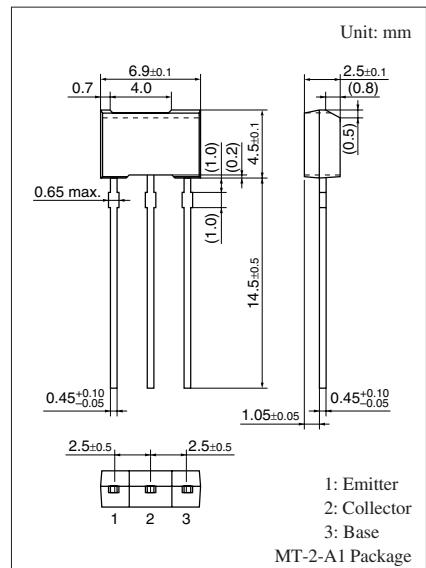
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

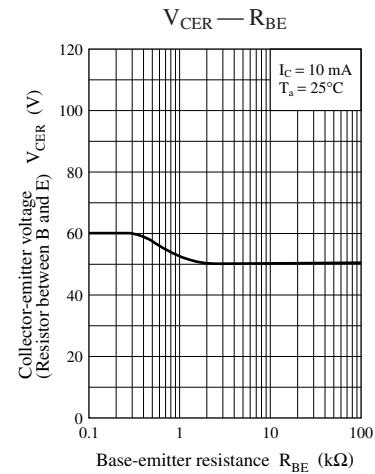
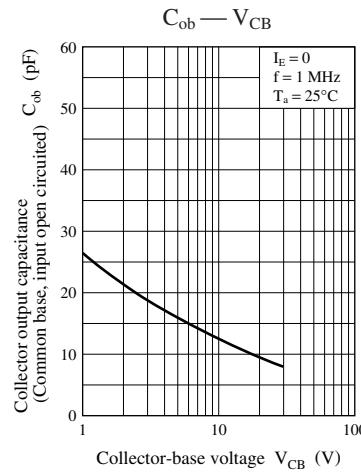
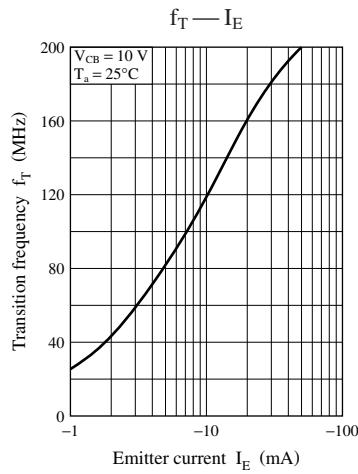
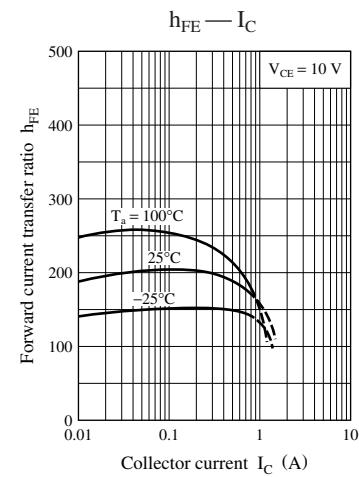
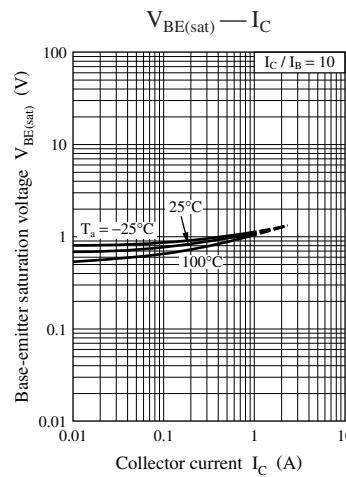
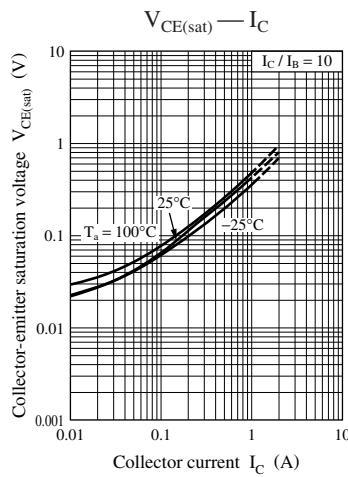
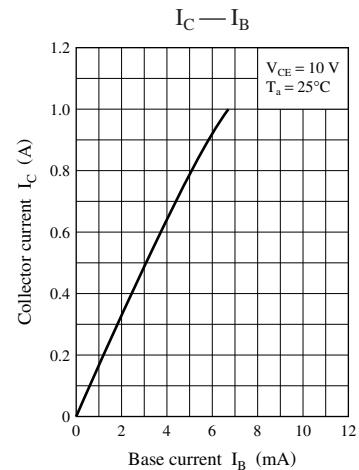
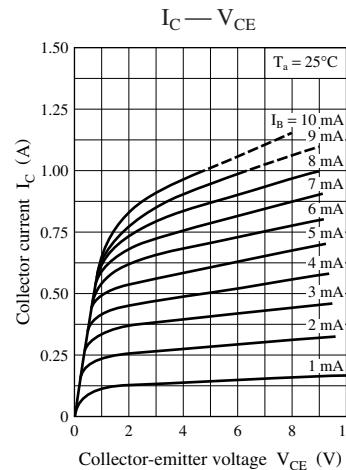
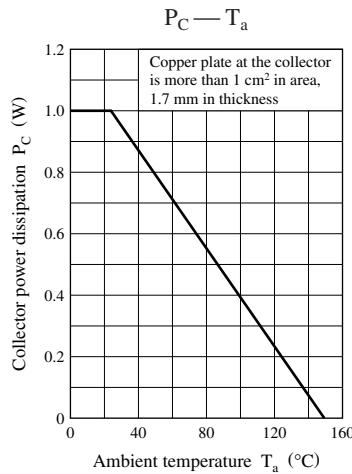
2. \*1: Pulse measurement

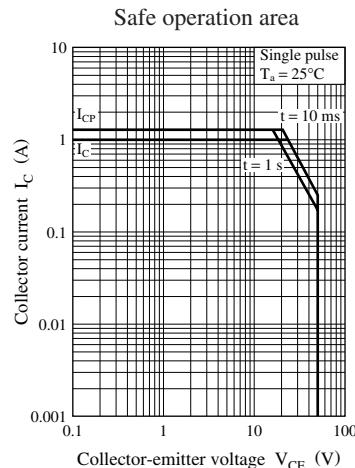
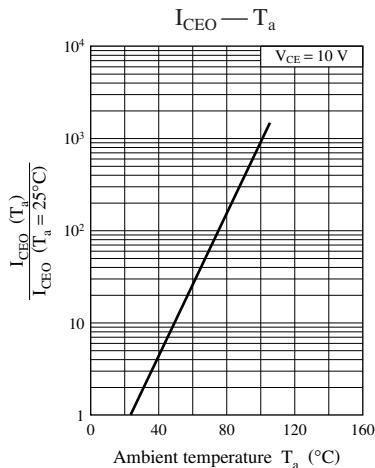
\*2: Rank classification

Rank	Q	R	S	No rank
$h_{FE1}$	85 to 170	120 to 240	170 to 340	85 to 340

Product of no-rank classification is not marked.







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